

**DESCRIPTION**

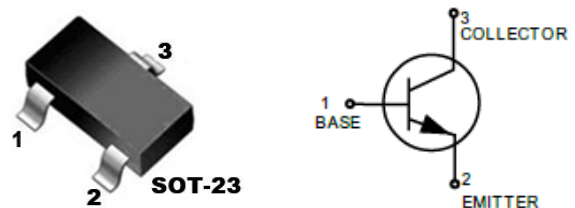
The BC847BL-Q is available in SOT-23 package.

FEATURE

- AEC-Q101 qualified
- ESD Rating: Human Body Model: >4000 V, Machine Model: >400 V

ORDERING INFORMATION

Package Type	Part Number
SOT-23	BC847BL-Q
Note	SPQ: 3,000pcs/Reel
AiT provides all RoHS Compliant Products	

PIN DESCRIPTION

PIN#	DESCRIPTION
1	BASE
2	EMITTER
3	COLLECTOR

ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$, unless otherwise noted.

V_{CEO} , Collector–Emitter Voltage	45V	
V_{CBO} , Collector–Base Voltage	50V	
V_{EBO} , Emitter–Base Voltage	6V	
I_C , Collector Current — Continuous	100mA	
P_D , Total Device Dissipation	@ $T_A = 25^\circ\text{C}$	225mW
	Derate above 25°C	1.8mW/ $^\circ\text{C}$
$R_{\theta JA}$, Thermal Resistance, Junction–to–Ambient	556 $^\circ\text{C}/\text{W}$	
P_D , Total Device Dissipation with Alumina Substrate (dimension: 0.4x0.3x0.024 mm)	@ $T_A = 25^\circ\text{C}$	300mW
	Derate above 25°C	2.5mW/ $^\circ\text{C}$
$R_{\theta JA}$, Thermal Resistance, Junction–to–Ambient	417 $^\circ\text{C}/\text{W}$	
T_J , Junction Temperature Range	-55 $^\circ\text{C}$ ~+150 $^\circ\text{C}$	
T_{STG} , Storage Temperature Range	-55 $^\circ\text{C}$ ~+150 $^\circ\text{C}$	

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**ELECTRICAL CHARACTERISTICS**T_A = 25°C, unless otherwise noted.

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Collector–Emitter Breakdown Voltage	V _{BR(CEO)}	I _C = 10mA	45	-	-	V
Collector–Emitter Breakdown Voltage	V _{BR(CES)}	I _C = 10μA, V _{EB} = 0	50	-	-	V
Collector–Base Breakdown Voltage	V _{BR(CBO)}	I _C = 10μA	50	-	-	V
Emitter–Base Breakdown Voltage	V _{BR(EBO)}	I _E = 1μA	6	-	-	V
Collector Cutoff Current	I _{CBO}	V _{CB} = 30V	-	-	15	nA
		V _{CB} = 30V, T _A = 150°C	-	-	5	μA
Emitter-Base cut-off current	I _{EBO}	I _C = 0, V _{EB} = 5V	-	-	100	nA
Collector-Emittter cutoff Current	I _{CEO}	V _{CE} = 45V, I _B = 0	-	-	2	mA
ON CHARACTERISTICS						
DC Current Gain	h _{FE}	I _C = 2mA, V _{CE} = 5V	200	290	450	-
Collector–Emitter Saturation Voltage	V _{CE(sat)}	I _C = 10mA, I _B = 0.5mA	-	-	0.25	V
		I _C = 100mA, I _B = 5mA	-	-	0.60	
Base–Emitter Saturation Voltage	V _{BE(sat)}	I _C = 10mA, I _B = 0.5mA	-	0.70	-	V
		I _C = 100mA, I _B = 5mA	-	0.90	-	
Base–Emitter Voltage	V _{BE(on)}	I _C = 2mA, I _B = 5mA	580	660	700	mV
		I _C = 10mA, I _B = 5mA	-	-	770	
SMALL-SIGNAL CHARACTERISTICS						
Output Capacitance	C _{obo}	V _{CB} = 10V, f = 1MHz	-	-	4.5	pF
Current-Gain-Bandwidth Product	f _T	V _{CE} = 5V, I _C = 10mA, f = 100MHz	100	-	-	MHz
Noise Figure	NF	I _C = 0.2mA, V _{CE} = 5V, R _S = 2 kΩ, f = 1kHz, B _W = 200Hz	-	-	10	dB



TYPICAL PERFORMANCE CHARACTERISTICS

Fig 1. HFE vs. IC (VCE=5.0V)

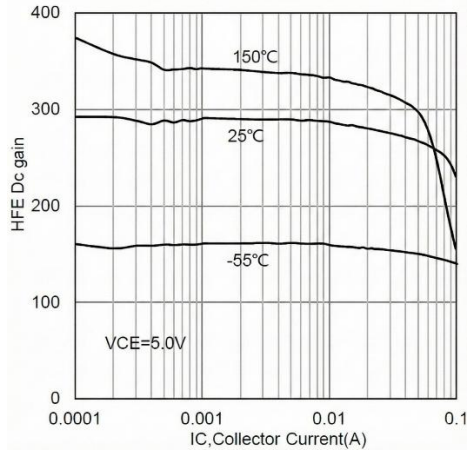


Fig 2. HFE vs. IC (VCE=10V)

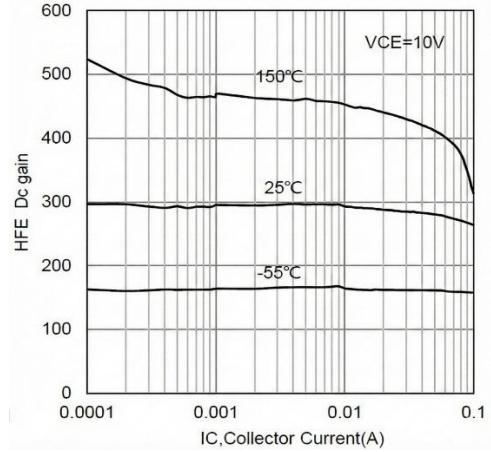


Fig 3. IC vs. VCE

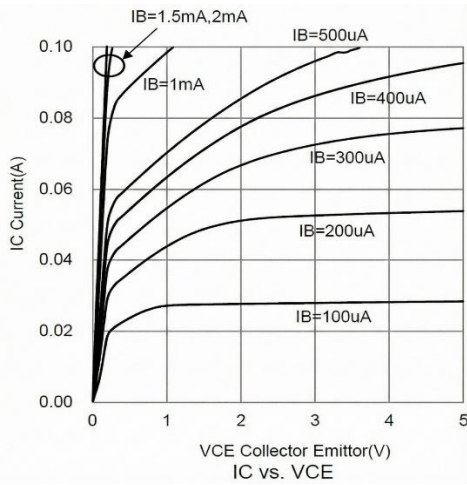


Fig 4. VCE vs. IB

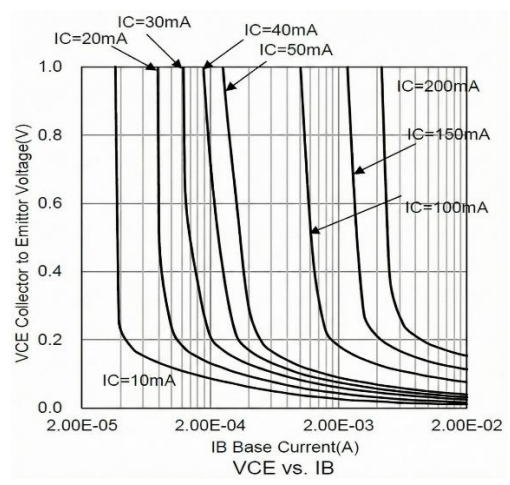


Fig 5. VBE (on) vs. IC

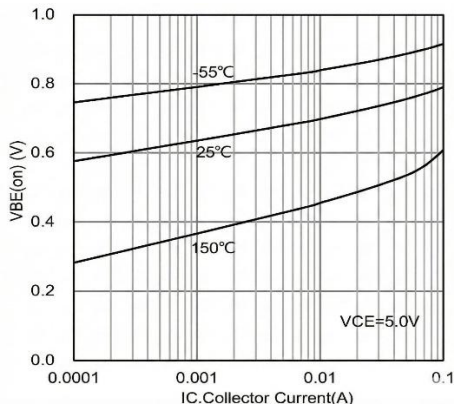


Fig 6. VBE (sat) vs. IC

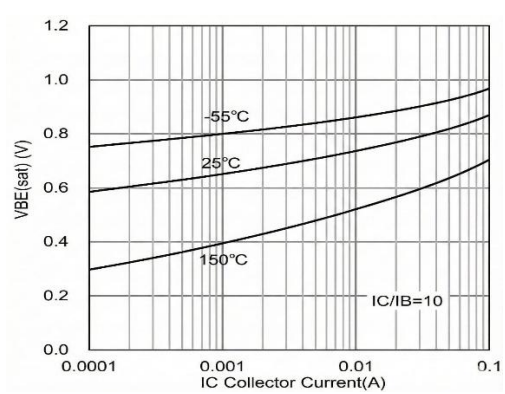




Fig 7. VCE (sat) vs. IC

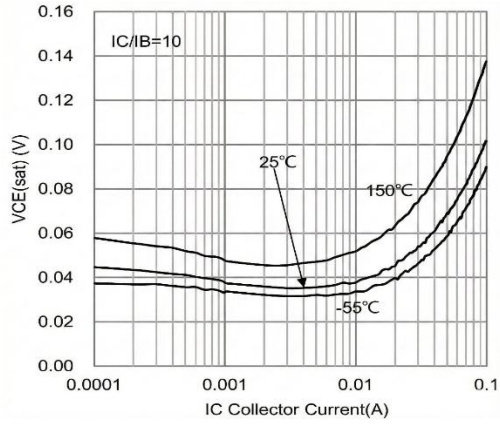
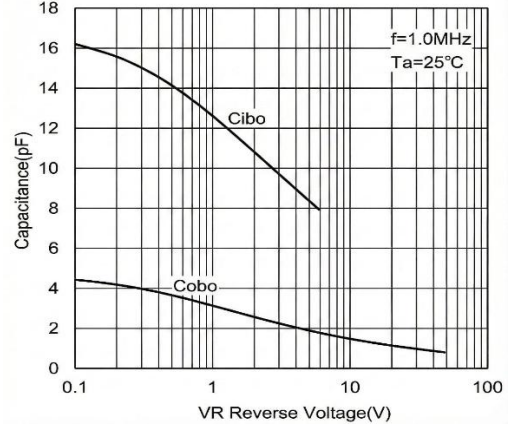


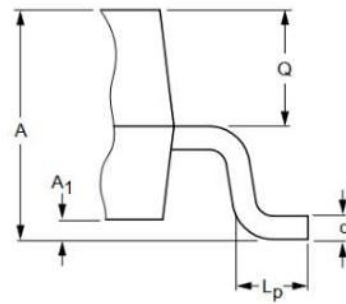
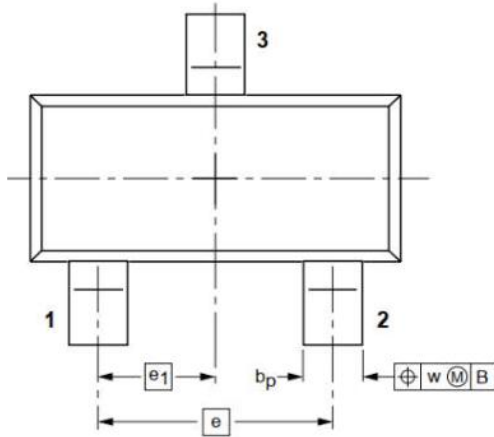
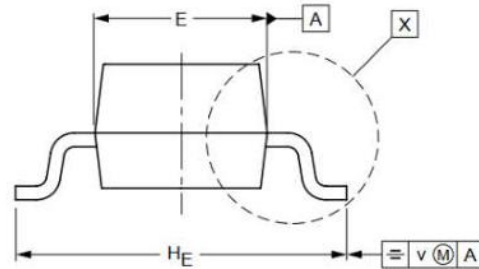
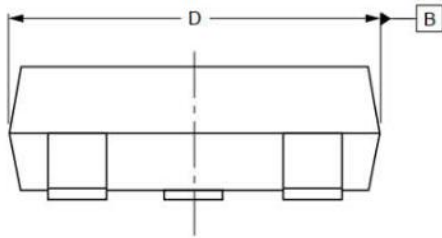
Fig 8. Capacitance



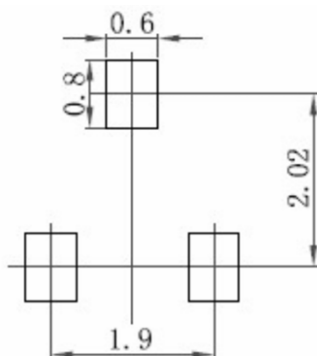


PACKAGE INFORMATION

Dimension in SOT-23 Package (Unit: mm)



detail X



The recommended mounting pad size

SYMBOL	MIN	MAX
A	0.900	1.150
A1	0.100	
bp	0.380	0.480
C	0.090	0.150
D	2.800	3.000
E	1.200	1.400
E	1.900	
E1	0.950	
HE	2.100	2.550
Lp	0.150	0.450
Q	0.450	0.550
V	0.200	
W	0.100	



IMPORTANT NOTICE

AiT Semiconductor Inc. (AiT) reserves the right to make changes to any its product, specifications, to discontinue any integrated circuit product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

AiT Semiconductor Inc. integrated circuit products are not designed, intended, authorized, or warranted to be suitable for use in life support applications, devices or systems or other critical applications. Use of AiT products in such applications is understood to be fully at the risk of the customer. As used herein may involve potential risks of death, personal injury, or server property, or environmental damage. In order to minimize risks associated with the customer's applications, the customer should provide adequate design and operating safeguards.

AiT Semiconductor Inc. assumes to no liability to customer product design or application support. AiT warrants the performance of its products of the specifications applicable at the time of sale.